

Technical Data

TRANSISTOR

maximum ratings

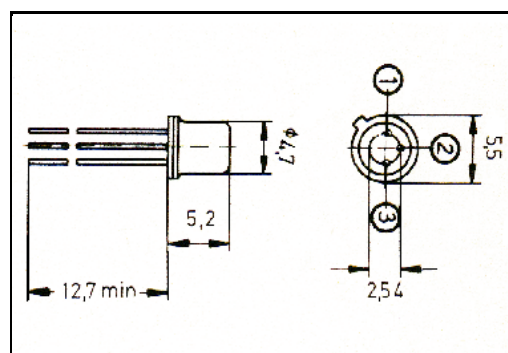
Voltage, Collector to Base (VCBO)	45.0	V	NO.	BCY79-9
Voltage, Collector to Emitter (VCE)	45.0	V	TYPE	PNP
Voltage, Emitter to Base (VEBO)	5.0	V		
Collector Current (IC)	0.2	A		
Base Current (IB)	0.02	A	CASE	TO-18
Max. Power Dissipation (PT) at TC = 45 °C	1.0	W		
Max. Thermal Resistance (Rth J-C)	150.0	°C/W		
Max. Junction Temperature (TJ)	200.0	°C		

PERFORMANCE CHARACTERISTICS at $T_c = 25^\circ\text{C}$, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	BVCEO	IC = 2.0 mA (1)	45.0	-	V
2.	BVEBO	IE = 1.0 μA	5.0	-	V
3.	ICES	VCE = 35.0 V	-	20.0	nA
4.	ICES	VCE = 35.0 V, TJ = 150.0° C	-	10.0	μA
5.	IEBO	VEB = 4.0 V	-	20.0	nA
6.	hFE	IC = 10.0 μA , VCE = 5.0 V (2)	40.0	-	-
7.	hFE	IC = 2.0 mA, VCE = 5.0 V (1)	250.0	460.0	-
8.	hFE	IC = 10.0 mA, VCE = 1.0 V (1)	160.0	630.0	-
9.	hFE	IC = 100.0 mA, VCE = 1.0 V (1)	60.0	-	-
10.	VCE(SAT)	IC = 10.0 mA, IB = 0.25 mA (1)	-	0.25	V
11.	VCE(SAT)	IC = 100.0 mA, IB = 2.5 mA (1)	-	0.8	V
12.	VBE(SAT)	IC = 10.0 mA, IB = 0.25 mA (1)	-	0.85	V
13.	VBE(SAT)	IC = 100.0 mA, IB = 2.5 mA (1)	-	1.2	V
14.	fT	IC = 10.0 mA, VCE = 5.0 V, f = 100.0 MHz (3)	180.0	-	MHz
15.	Cobo	VCB = 10.0 V	-	7.0	pF
16.	NF	IC = 0.2 mA, VCE = 5.0 V, f = 1.0 kHz	-	6.0	dB
17.					
18.					
19.					
20.					

Notes (1)pulse-tested $t_p \leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
 (2)typ. value / pulse-tested $t_p \leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
 (3)typical value

DIMENSIONS
in mm



Marking BCY79-9
 Customer GENERAL PURPOSE